

## NPN Transistors

## 2SD1252

## ■ Features

- High forward current transfer ratio  $hFE$   
which has satisfactory linearity
- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- Complementary to 2SB929

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

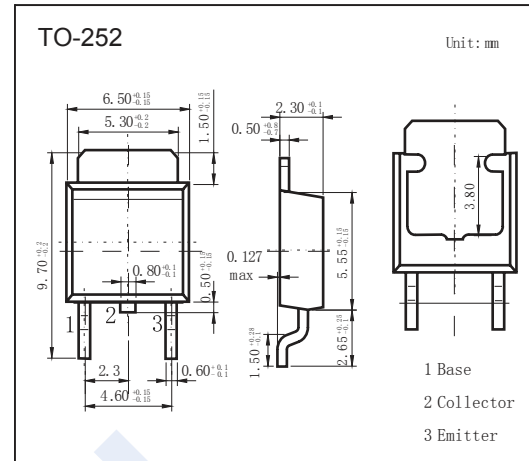
Parameter	Symbol	Rating	Unit	
Collector - Base Voltage	$V_{CBO}$	60	V	
Collector - Emitter Voltage	$V_{CEO}$	60		
Emitter - Base Voltage	$V_{EBO}$	6		
Collector Current - Continuous	$I_C$	3	A	
Collector Current - Pulse	$I_{CP}$	5		
Collector Power Dissipation	$P_C$	$T_c = 25^\circ\text{C}$	35	W
		$T_a = 25^\circ\text{C}$	1.3	
Junction Temperature	$T_J$	150	$^\circ\text{C}$	
Storage Temperature Range	$T_{stg}$	-55 to 150		

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_C = 100 \mu\text{A}$ , $I_E = 0$	60			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_C = 30 \text{ mA}$ , $I_B = 0$	60			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E = 100 \mu\text{A}$ , $I_C = 0$	6			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 60 \text{ V}$ , $I_E = 0$			0.1	mA
Collector cutoff current	$I_{CES}$	$V_{CB} = 60 \text{ V}$ , $I_E = 0$			200	
Collector cutoff current	$I_{CEO}$	$V_{CB} = 30 \text{ V}$ , $I_E = 0$			300	uA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5 \text{ V}$ , $I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 3 \text{ A}$ , $I_B = 375 \text{ mA}$			1.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 3 \text{ A}$ , $I_B = 375 \text{ mA}$			1.2	
Base - emitter voltage	$V_{BE}$	$V_{CE} = 4 \text{ V}$ , $I_C = 3 \text{ A}$			1.8	
DC current gain	$h_{FE(1)}$	$V_{CE} = 4 \text{ V}$ , $I_C = 1 \text{ A}$	40		250	
	$h_{FE(2)}$	$V_{CE} = 4 \text{ V}$ , $I_C = 3 \text{ A}$	10			
Turn-on time	$t_{on}$	$I_C = 1 \text{ A}$ , $I_{B1} = 0.1 \text{ A}$ , $I_{B2} = -0.1 \text{ A}$ , $V_{CC} = 50 \text{ V}$		0.5		us
Storage time	$t_{stg}$			2.5		
Fall time	$t_f$				0.4	
Transition frequency	$f_T$	$V_{CE} = 5 \text{ V}$ , $I_C = 500 \text{ mA}$ , $f = 10 \text{ MHz}$		30		MHz

■ Classification of  $h_{FE(1)}$ 

Type	2SD1252-R	2SD1252-Q	2SD1252-P
Marking	40-90	70-150	120-250



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■ Typical Characteristics

